

100V N-Ch Power MOSFET
Feature

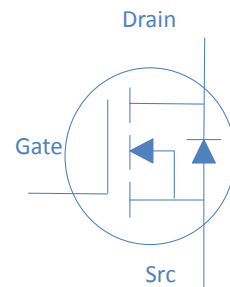
- ◇ Optimized for high speed smooth switching
- ◇ Enhanced Body diode dv/dt capability
- ◇ Enhanced Avalanche Ruggedness
- ◇ 100% UIS Tested, 100% Rg Tested
- ◇ Lead Free

Application

- ◇ DC-DC Conversion
- ◇ Hard Switching and High Speed Circuit
- ◇ Power Tools
- ◇ UPS
- ◇ SSR

V_{DS}		100	V
$R_{DS(on),typ}$	TO-263	3.4	m Ω
$R_{DS(on),typ}$	TO-220	3.7	m Ω
I_D (Silicon Limited)		167	A

TO-263

TO-220


Part Number	Package	Marking
HGB042N10A	TO-263	GB042N10A
HGP042N10A	TO-220	GP042N10A

Absolute Maximum Ratings at $T_J=25^\circ\text{C}$ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	$T_C=25^\circ\text{C}$	167	A
		$T_C=100^\circ\text{C}$	118	
Drain to Source Voltage	V_{DS}	-	100	V
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	450	A
Avalanche Energy, Single Pulse	E_{AS}	$L=0.1\text{mH}, T_C=25^\circ\text{C}$	180	mJ
Power Dissipation	P_D	$T_C=25^\circ\text{C}$	231	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to 175	$^\circ\text{C}$

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Case	$R_{\theta JC}$	0.65	$^\circ\text{C/W}$
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	60	$^\circ\text{C/W}$

Electrical Characteristics at T_j=25°C (unless otherwise specified)
Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250μA	2	3	4	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} =0V, V _{DS} =100V, T _j =25°C	-	-	1	μA
		V _{GS} =0V, V _{DS} =100V, T _j =100°C	-	-	100	
Gate to Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Drain to Source on Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	3.4	3.9	mΩ
Drain to Source on Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A				
Transconductance	g _{fs}	V _{DS} =5V, I _D =20A	-	50	-	S
Gate Resistance	R _G	V _{GS} =0V, V _{DS} Open, f=1MHz	-	1.3	-	Ω

Dynamic Characteristics

Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =50V, f=1MHz	-	3650	-	pF
Output Capacitance	C _{oss}		-	1110	-	
Reverse Transfer Capacitance	C _{rss}		-	43	-	
Total Gate Charge	Q _g	V _{DD} =50V, I _D =20A, V _{GS} =10V	-	75	-	nC
Gate to Source Charge	Q _{gs}		-	10	-	
Gate to Drain (Miller) Charge	Q _{gd}		-	34	-	
Turn on Delay Time	t _{d(on)}	V _{DD} =50V, I _D =20A, V _{GS} =10V, R _G =10Ω,	-	13	-	ns
Rise time	t _r		-	19	-	
Turn off Delay Time	t _{d(off)}		-	45	-	
Fall Time	t _f		-	27	-	

Reverse Diode Characteristics

Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _F =20A	-	0.9	1.2	V
Reverse Recovery Time	t _{rr}	V _R =50V, I _F =20A, dI _F /dt=500A/μs	-	50	-	ns
Reverse Recovery Charge	Q _{rr}		-	275	-	nC

Fig 1. Typical Output Characteristics

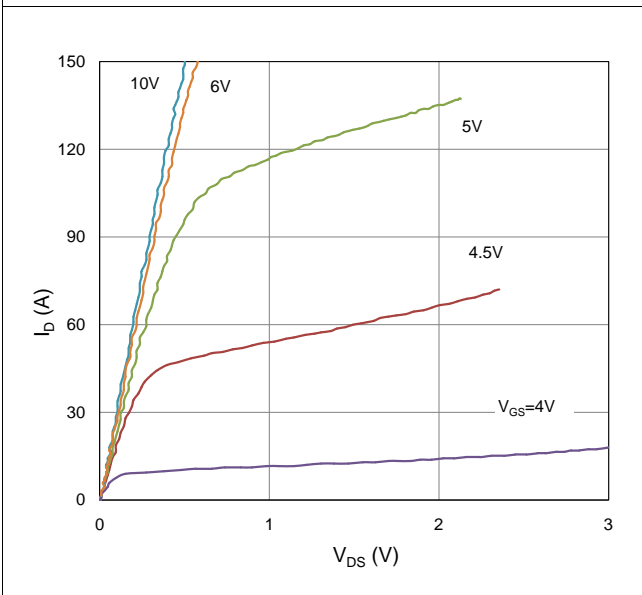


Figure 2. On-Resistance vs. Gate-Source Voltage

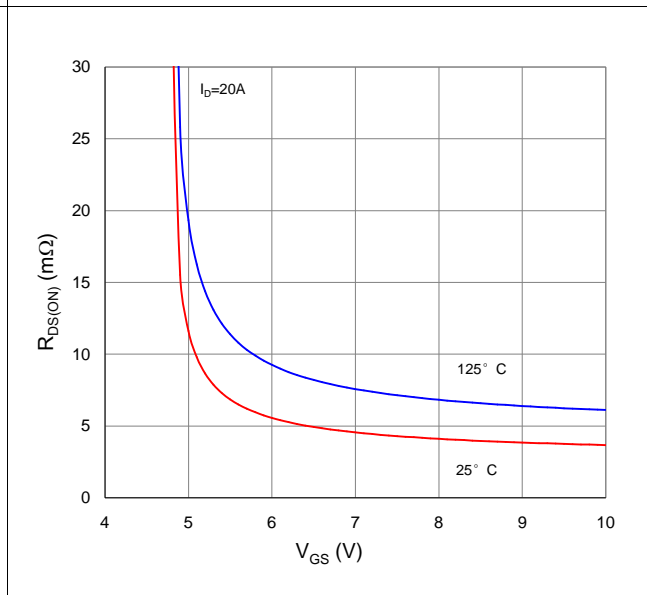


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

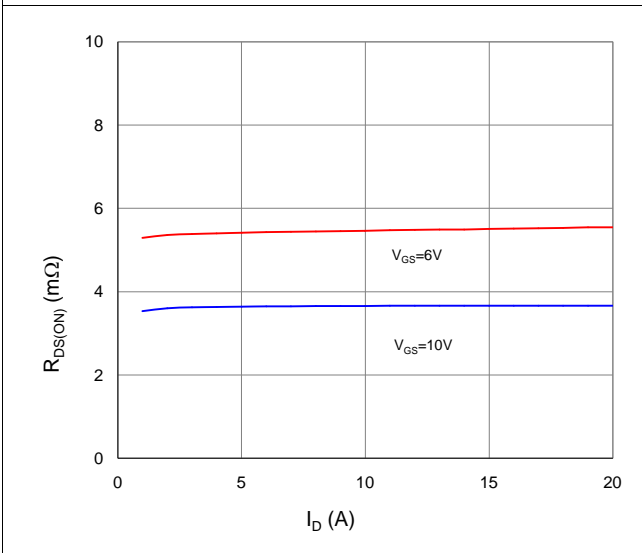


Figure 4. Normalized On-Resistance vs. Junction Temperature

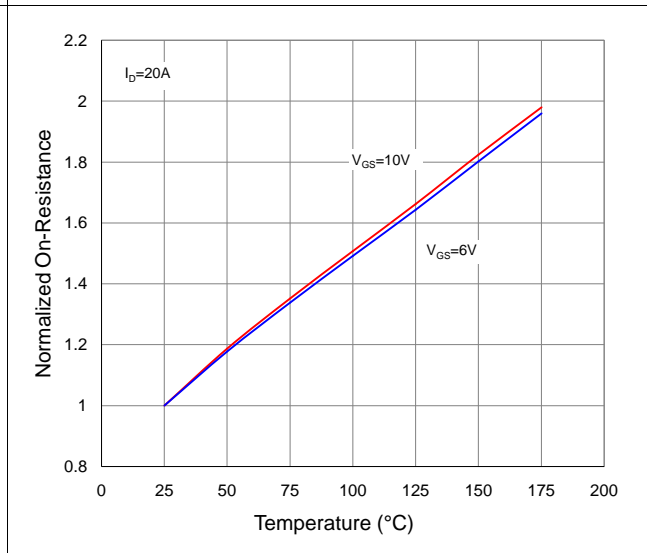


Figure 5. Typical Transfer Characteristics

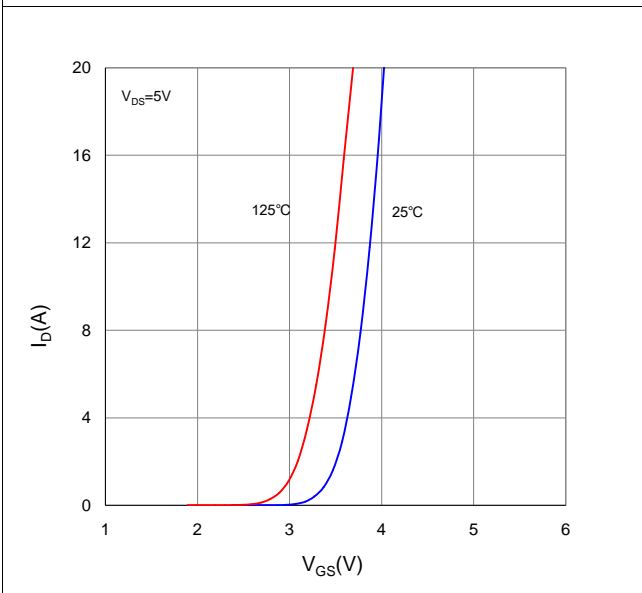


Figure 6. Typical Source-Drain Diode Forward Voltage

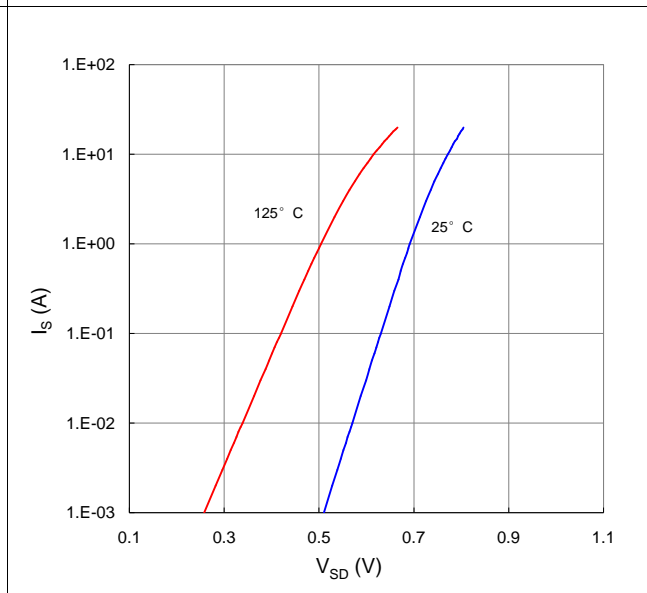


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

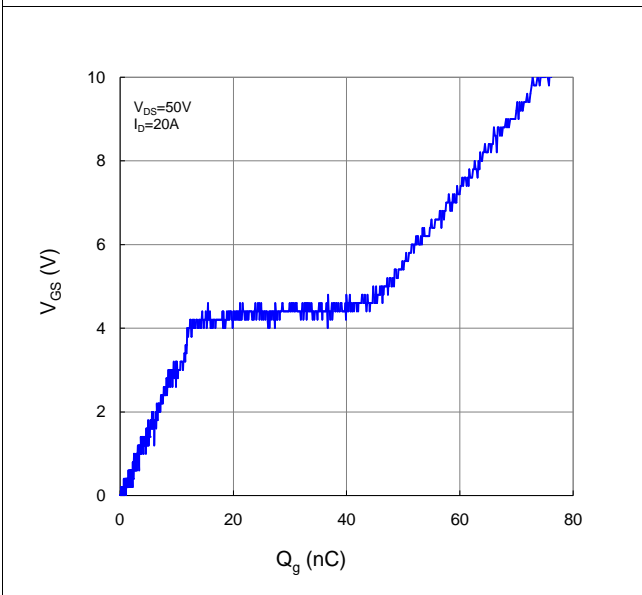


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

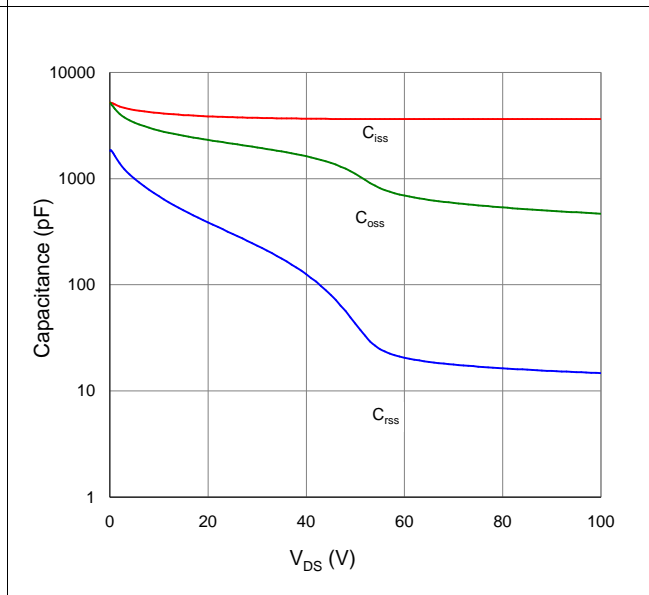


Figure 9. Maximum Safe Operating Area

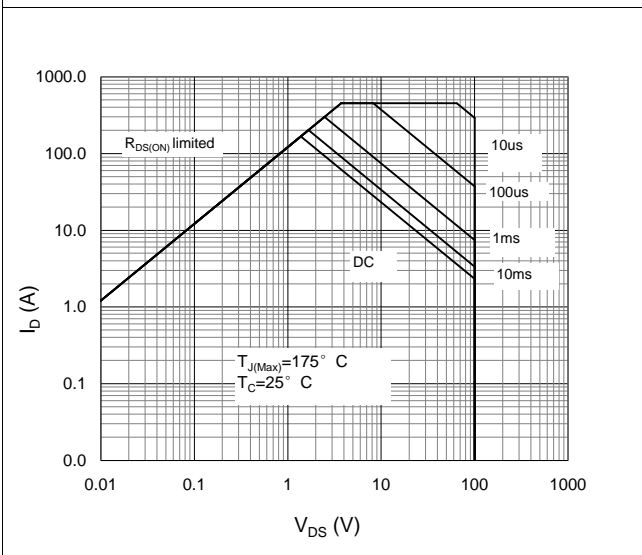


Figure 10. Maximum Drain Current vs. Case Temperature

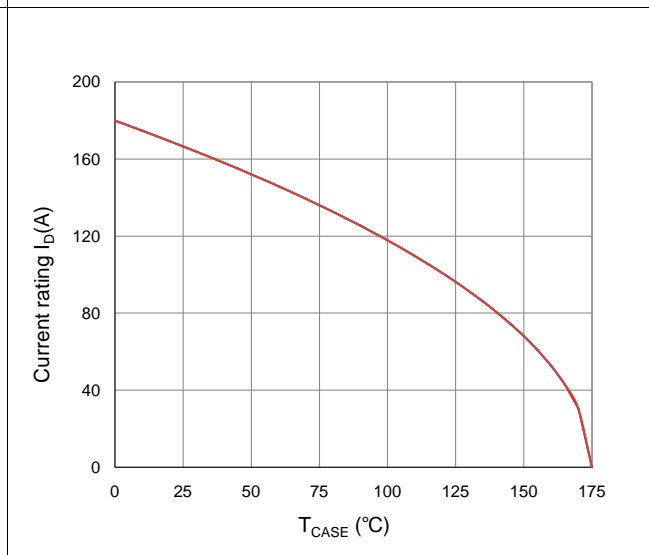
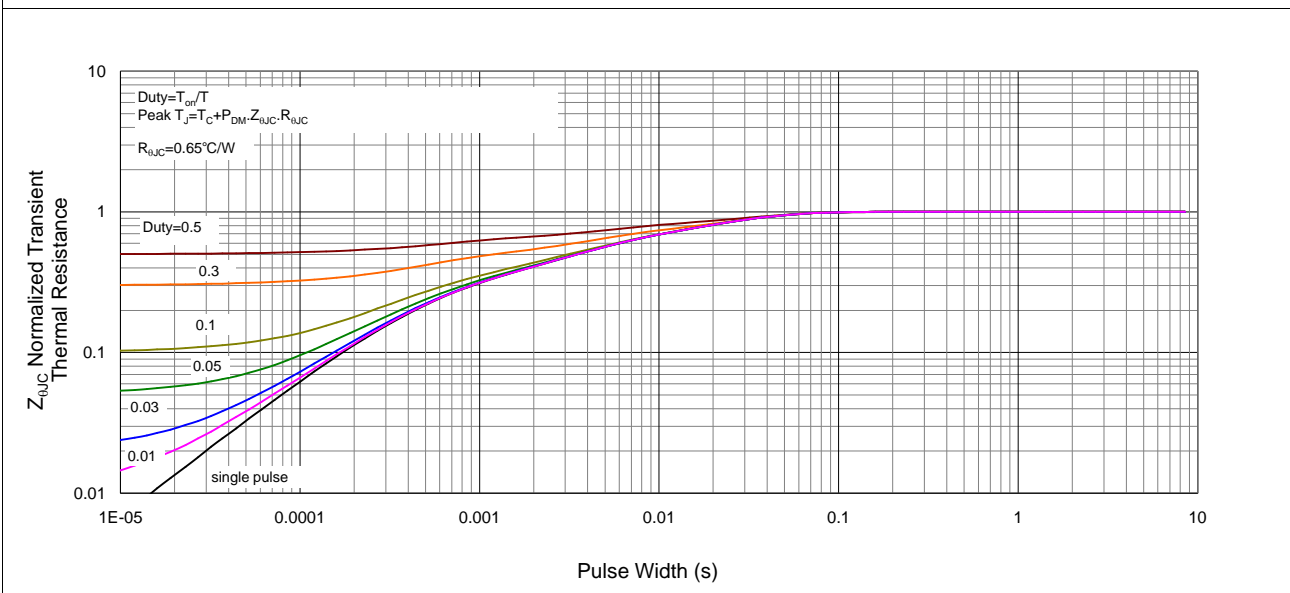
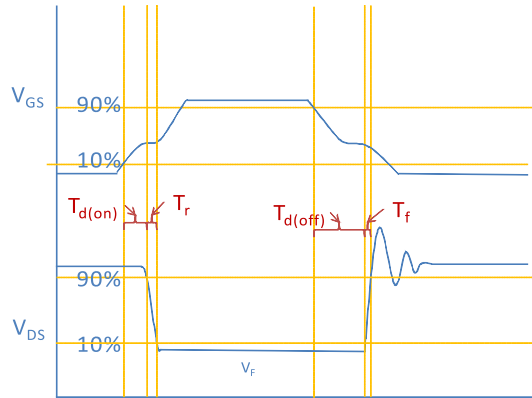
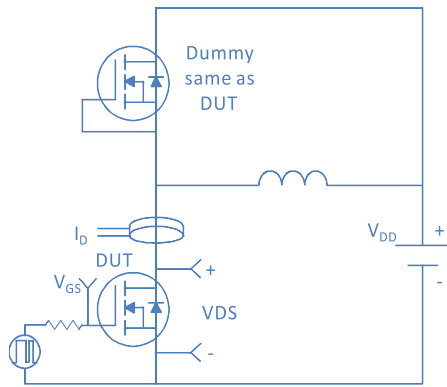


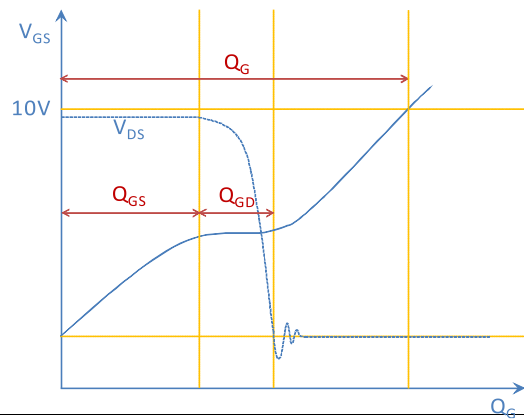
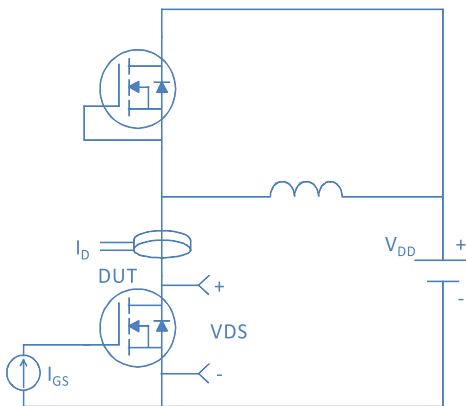
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case



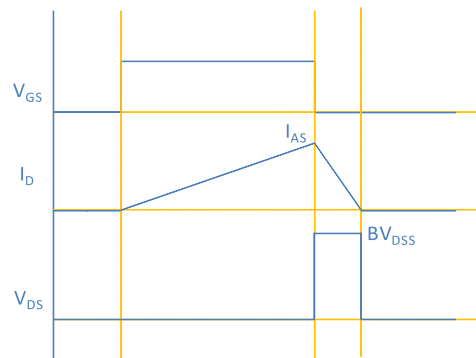
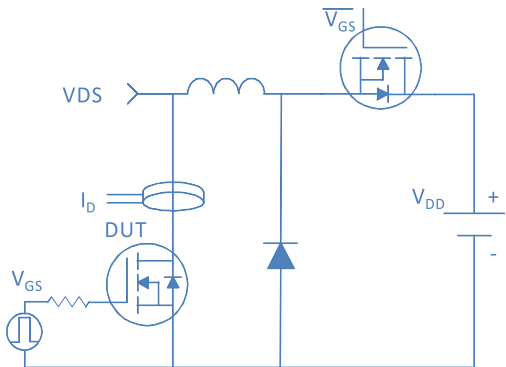
Inductive switching Test



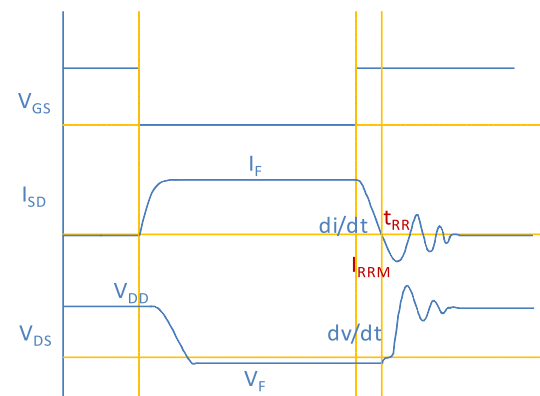
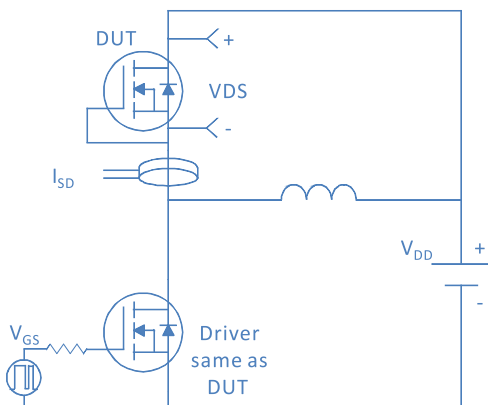
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

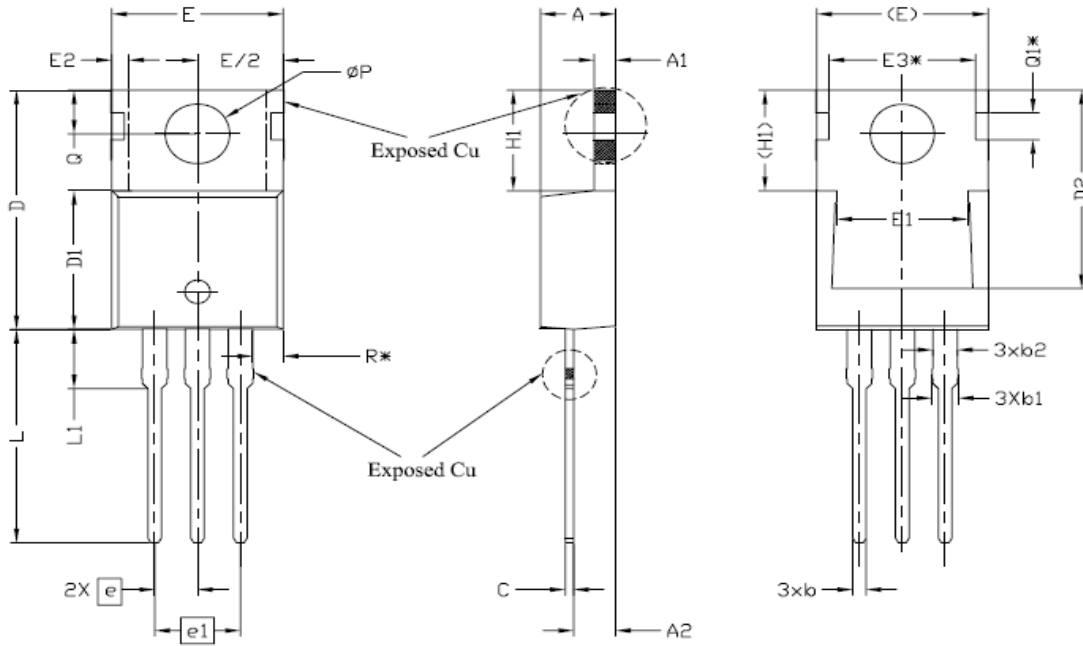


Diode Recovery Test



Package Outline

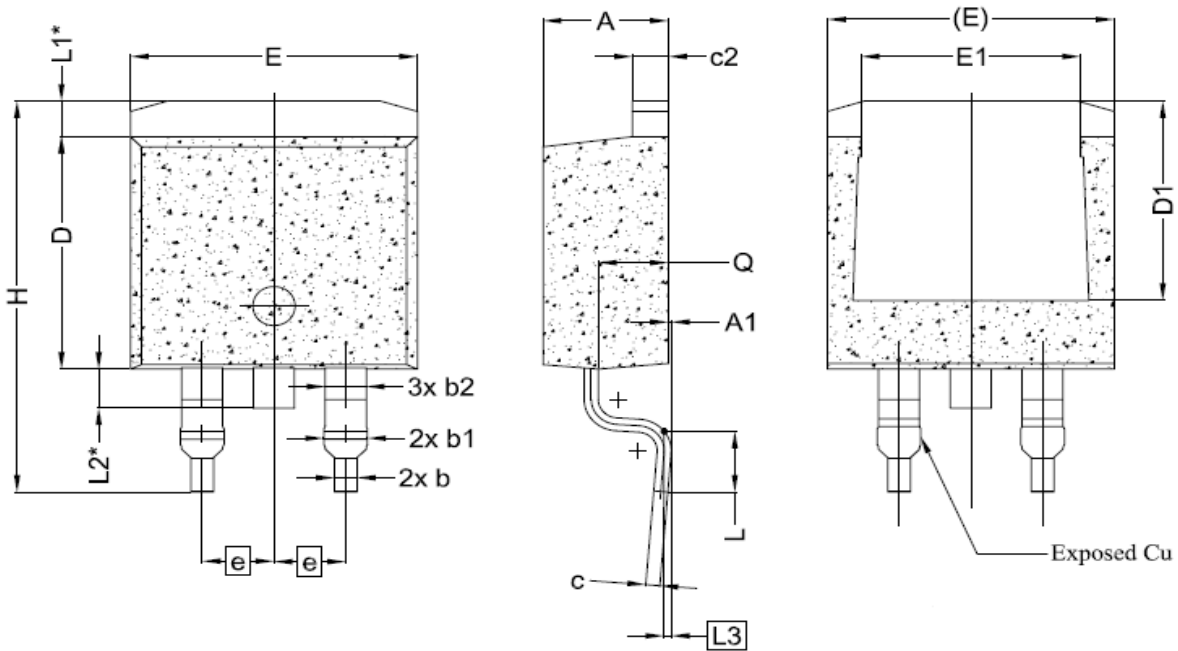
TO-220, 3 leads



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4,24	4,44	4,64	
A1	1,15	1,27	1,40	
A2	2,30	2,48	2,70	
b	0,70	0,80	0,90	
b1	1,20	1,55	1,75	
b2	1,20	1,45	1,70	
c	0,40	0,50	0,60	
D	14,70	15,37	16,00	4
D1	8,82	8,92	9,02	
D2	12,63	12,73	12,83	5
E	9,96	10,16	10,36	4,5
E1	6,86	7,77	8,89	5
E2	-	-	0,76	6
E3*	8,70REF.			
e	2,54BSC			
e1	5,08BSC			
H1	6,30	6,45	6,60	5,6
L	13,47	13,72	13,97	
L1	3,60	3,80	4,00	
ϕP	3,75	3,84	3,93	
Q	2,60	2,80	3,00	
Q1*	1,73REF.			
R*	1,82REF.			

Package Outline

TO-263, 3 leads



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	—
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70